



2SB1030 (3CG1030)
2SB1030A (3CG1030A)

硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途:用于低频功率放大,与 2SD1423 (3DG1423)/2SD1423A (3DG1423A) 互补.

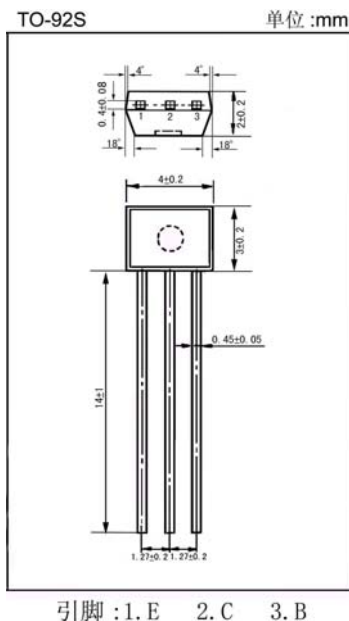
Purpose: Low frequency power amplifier, complementary to 2SD1423 (3DG1423)/2SD1423A (3DG1423A).

特点:体积小最适合高密度装配。

Features: Optimum for high-density mounting.

极限参数/Absolute Maximum Ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO} 2SB1030 2SB1030A	-30 -60	V
V _{CEO} 2SB1030 2SB1030A	-25 -50	V
V _{EBO}	-7.0	V
I _C	-0.5	A
I _{CP}	-1.0	A
P _C	300	mW
T _j	150	°C
T _{stg}	-55~150	°C



电性能参数/Electrical Characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test Condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CBO} 2SB1030 2SB1030A	I _C =-10 μA I _E =0	-30 -60			V
V _{CEO} 2SB1030 2SB1030A	I _C =-2.0mA I _B =0	-25 -50			V
V _{EBO}	I _E =-10 μA I _C =0	-7.0			V
I _{CBO}	V _{CB} =-20V I _E =0			-0.1	μA
I _{CEO}	V _{CE} =-20V I _B =0			-1.0	μA
h _{FE(1)}	V _{CE} =-10V I _C =-150mA	85		340	
h _{FE(2)}	V _{CE} =-10V I _C =-500mA	40			
V _{CE(sat)}	I _C =-300mA I _B =-30mA		-0.35	-0.6	V
f _T	V _{CB} =-10V I _E =50mA f=200MHz		200		MHz
C _{ob}	V _{CB} =-10V I _E =0 f=1.0MHz		6.0	15	pF

h_{FE(1)} 分档/h_{FE(1)} Classifications: Q: 85~170 R: 120~240 S: 170~340



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